TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

## **GT50N322A**

# Voltage Resonance Inverter Switching Application Fifth Generation IGBT

· FRD included between emitter and collector

• Enhancement mode type

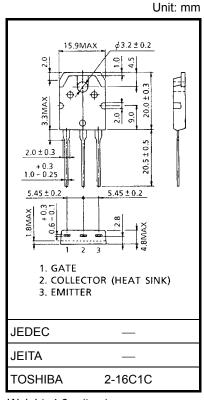
• High speed IGBT :  $t_f = 0.10 \mu s$  (typ.) ( $I_C = 60 A$ )

FRD :  $t_{rr} = 0.8 \mu s$  (typ.) (di/dt = -20 A/ $\mu s$ )

Low saturation voltage: V<sub>CE</sub> (sat) = 2.2 V (typ.) (I<sub>C</sub> = 60 A)

#### Absolute Maximum Ratings (Ta = 25°C)

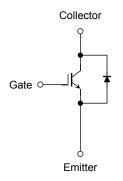
| Characteristics                                    |     | Symbol           | Rating     | Unit |  |
|--|-----|------------------|------------|------|--|
| Collector-emitter voltage                          |     | V <sub>CES</sub> | 1000       | V    |  |
| Gate-emitter voltage                               |     | V <sub>GES</sub> | ± 25       | V    |  |
| Collector current                                  | DC  | IC               | 50         | А    |  |
|  | 1ms | I <sub>CP</sub>  | 120        |      |  |
| Diode forward current                              | DC  | lF               | 15         | Α    |  |
|  | 1ms | I <sub>FP</sub>  | 120        |      |  |
| Collector power dissipation ( $Tc = 25^{\circ}C$ ) |     | P <sub>C</sub>   | 156        | W    |  |
| Junction temperature                               |     | Tj               | 150        | °C   |  |
| Storage temperature                                |     | T <sub>stg</sub> | -55 to 150 | °C   |  |



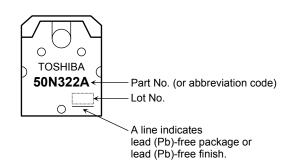
Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Equivalent Circuit**



#### Marking

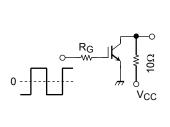


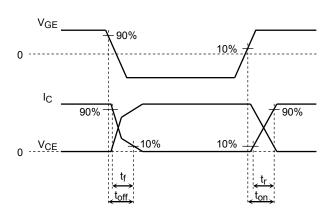
## Electrical Characteristics (Ta = 25°C)

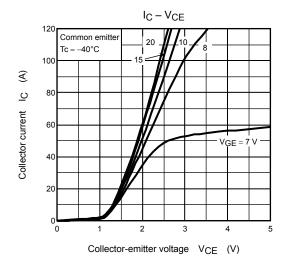
| Characteristics                      |               | Symbol                | Test Condition  | Min | Тур. | Max   | Unit |
|--------------------------------------|---------------|-----------------------|---|-----|------|-------|------|
| Gate leakage cur                     | rent          | I <sub>GES</sub>      | $V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$                             | _   | _    | ± 500 | nA   |
| Collector cut-off current            |               | I <sub>CES</sub>      | V <sub>CE</sub> = 1000 V, V <sub>GE</sub> = 0                       | _   | _    | 1.0   | mA   |
| Gate-emitter cut-off voltage         |               | V <sub>GE</sub> (OFF) | $I_C = 60 \text{ mA}, V_{CE} = 5 \text{ V}$                         | 3.0 | _    | 6.0   | V    |
| Collector-emitter saturation voltage |               | V <sub>CE</sub> (sat) | I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15 V                       | _   | 2.2  | 2.8   | V    |
| Input capacitance                    |               | C <sub>ies</sub>      | V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz              | _   | 4000 | _     | pF   |
| Switching time                       | Rise time     | t <sub>r</sub>        | Resistive Load  | _   | 0.23 | _     | μs   |
|                                      | Turn-on time  | t <sub>on</sub>       | V <sub>CC</sub> = 600 V, I <sub>C</sub> = 60 A                      | _   | 0.33 | _     |      |
|                                      | Fall time     | t <sub>f</sub>        | $V_{GG} = \pm 15 \text{ V}, R_G = 51 \Omega$                        | _   | 0.10 | 0.25  |      |
|                                      | Turn-off time | t <sub>off</sub>      | (Note 1)  | _   | 0.70 | _     |      |
| Diode forward voltage                |               | V <sub>F</sub>        | I <sub>F</sub> = 15 A, V <sub>GE</sub> = 0                          | _   | 1.2  | 1.9   | V    |
| Reverse recovery time                |               | t <sub>rr</sub>       | $I_F = 15 \text{ A}, V_{GE} = 0, di/dt = -20 \text{ A/}\mu\text{s}$ | _   | 0.8  | _     | μs   |
| Thermal Resistance R                 |               | Rth(j-c)              | _   | _   | _    | 0.8   | °C/W |
| Thermal Resistance                   |               | Rth(j-c)              | _   | _   | _    | 4.0   | °C/W |

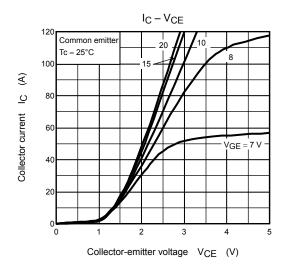
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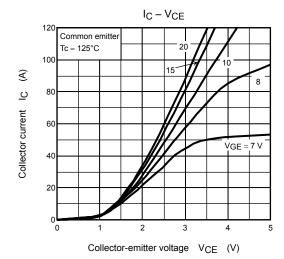
Note 1: Switching time measurement circuit and input/output waveforms

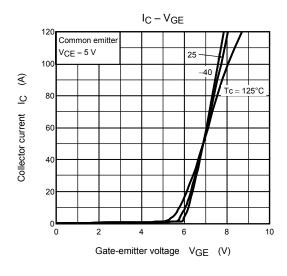


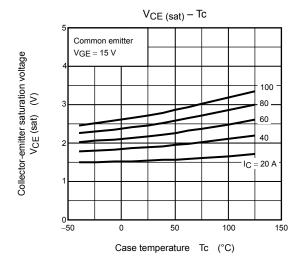


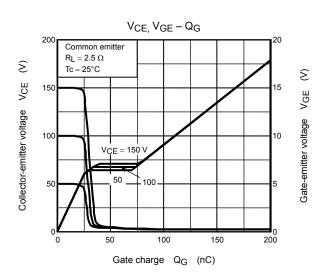


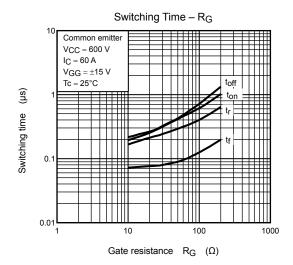


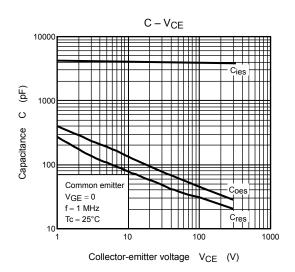


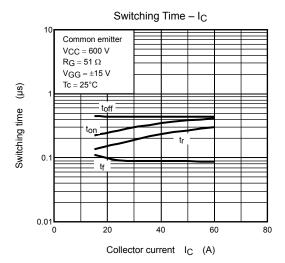


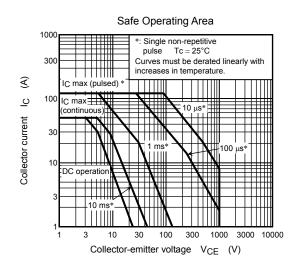


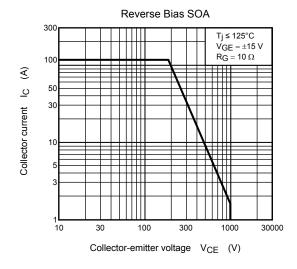


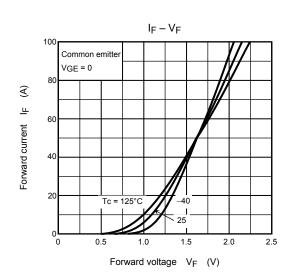


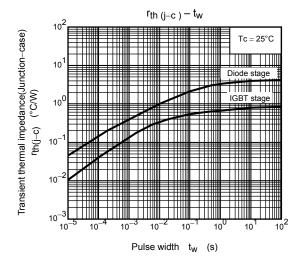


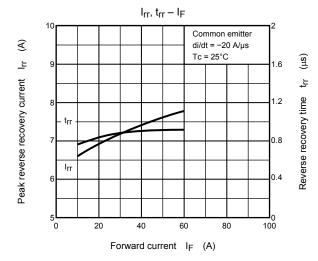


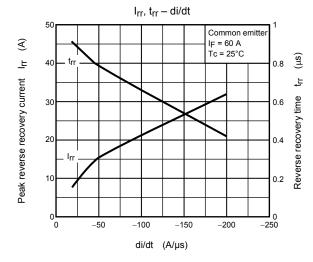












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